



BT234X-600E

4Q Triac

Rev. 1 — 12 October 2011

Product data sheet

1. Product profile

1.1 General description

Planar passivated four quadrant triac in a SOT186A (TO-220F) "full pack" plastic package intended for use in general purpose bidirectional switching and phase control applications. This sensitive gate "series E" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

1.2 Features and benefits

- Direct triggering from low power drivers and logic ICs
- High blocking voltage capability
- Isolated package
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate for easy logic level triggering
- Triggering in all four quadrants

1.3 Applications

- General purpose motor control
- General purpose switching

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	600	V
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 20\text{ ms}$; see Figure 4 ; see Figure 5	-	-	35	A
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_h \leq 98\text{ °C}$; see Figure 1 ; see Figure 2 ; see Figure 3	-	-	4	A
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; see Figure 7	-	-	10	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; see Figure 7	-	-	10	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ °C}$; see Figure 7	-	-	10	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G+; $T_j = 25\text{ °C}$; see Figure 7	-	-	25	mA



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		
2	T2	main terminal 2		
3	G	gate		
mb	n.c.	mounting base; isolated		

SOT186A (TO-220F)

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BT234X-600E	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_h \leq 98\text{ °C}$; see Figure 1 ; see Figure 2 ; see Figure 3	-	4	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25\text{ °C}$; $t_p = 20\text{ ms}$; see Figure 4 ; see Figure 5	-	35	A
		full sine wave; $T_{j(\text{init})} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$	-	38.5	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; sine-wave pulse	-	6.1	A^2s
di_T/dt	rate of rise of on-state current	$I_T = 7\text{ A}$; $I_G = 0.2\text{ A}$; $di_G/dt = 0.2\text{ A}/\mu s$; T2+ G+	-	50	$A/\mu s$
		$I_T = 7\text{ A}$; $I_G = 0.2\text{ A}$; $di_G/dt = 0.2\text{ A}/\mu s$; T2+ G-	-	50	$A/\mu s$
		$I_T = 7\text{ A}$; $I_G = 0.2\text{ A}$; $di_G/dt = 0.2\text{ A}/\mu s$; T2- G-	-	50	$A/\mu s$
		$I_T = 7\text{ A}$; $I_G = 0.2\text{ A}$; $di_G/dt = 0.2\text{ A}/\mu s$; T2- G+	-	10	$A/\mu s$
I_{GM}	peak gate current		-	2	A
P_{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T_{stg}	storage temperature		-40	150	$^{\circ}C$
T_j	junction temperature		-	125	$^{\circ}C$

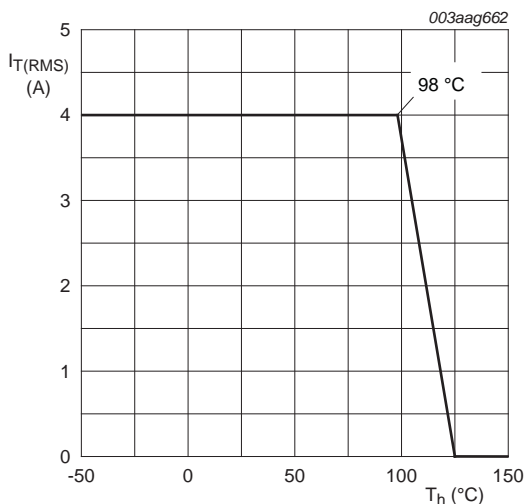


Fig 1. RMS on-state current as a function of heatsink temperature; maximum values

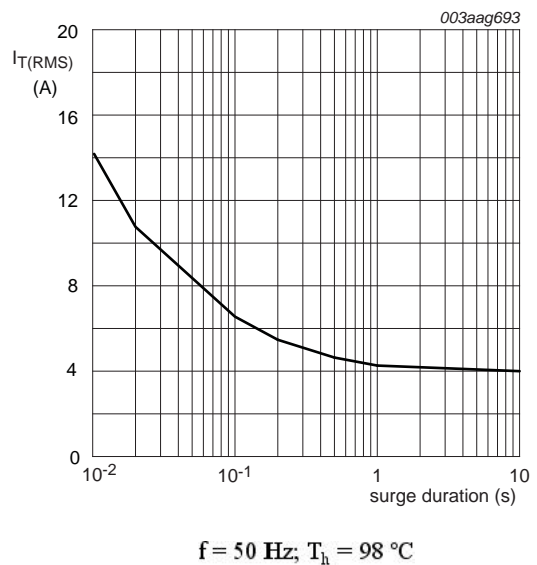


Fig 2. RMS on-state current as a function of surge duration; maximum values

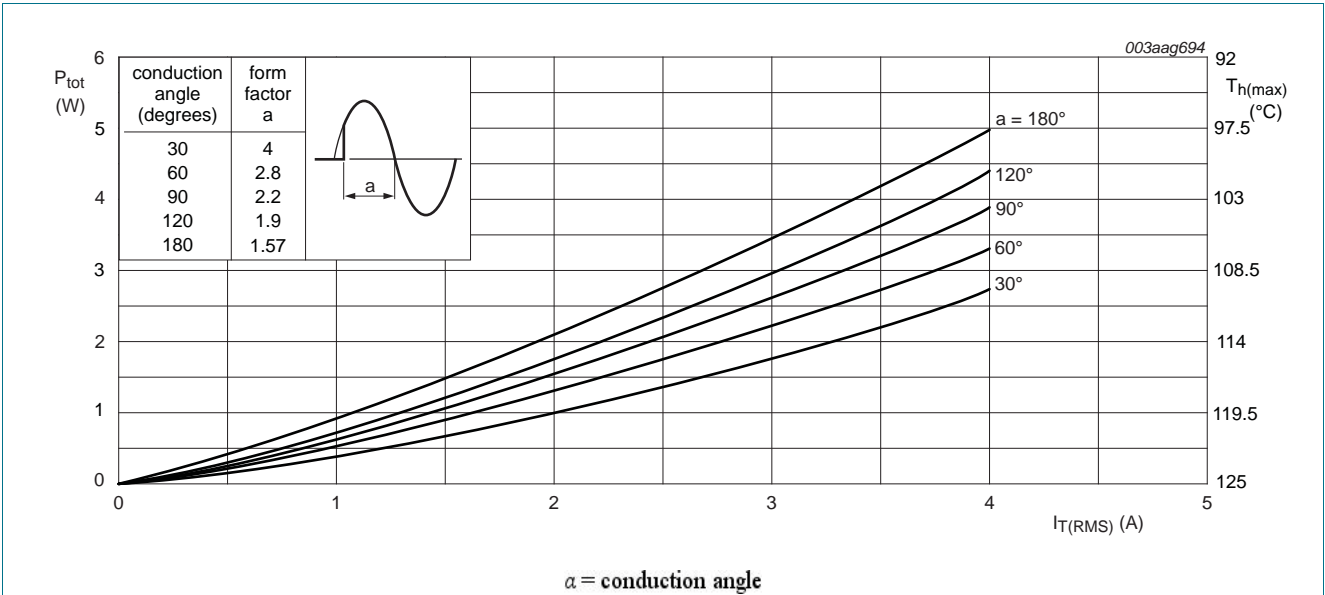


Fig 3. Total power dissipation as a function of RMS on-state current; maximum values

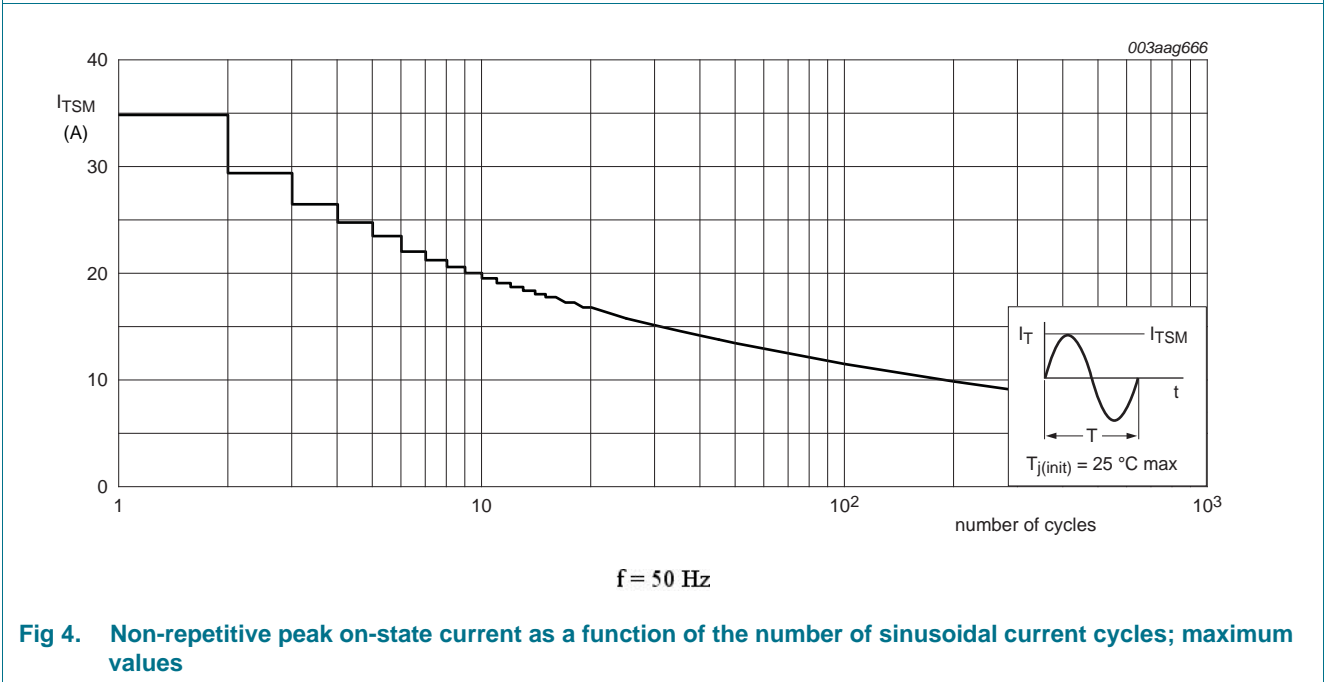
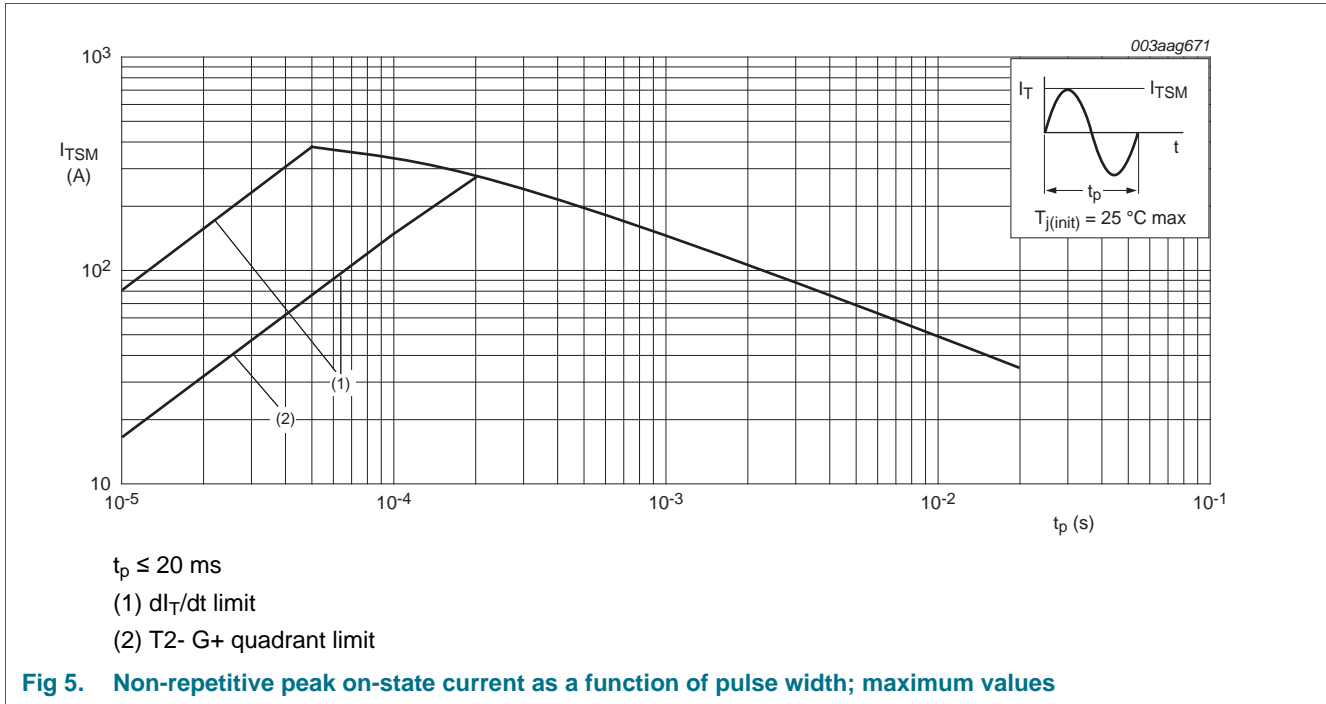


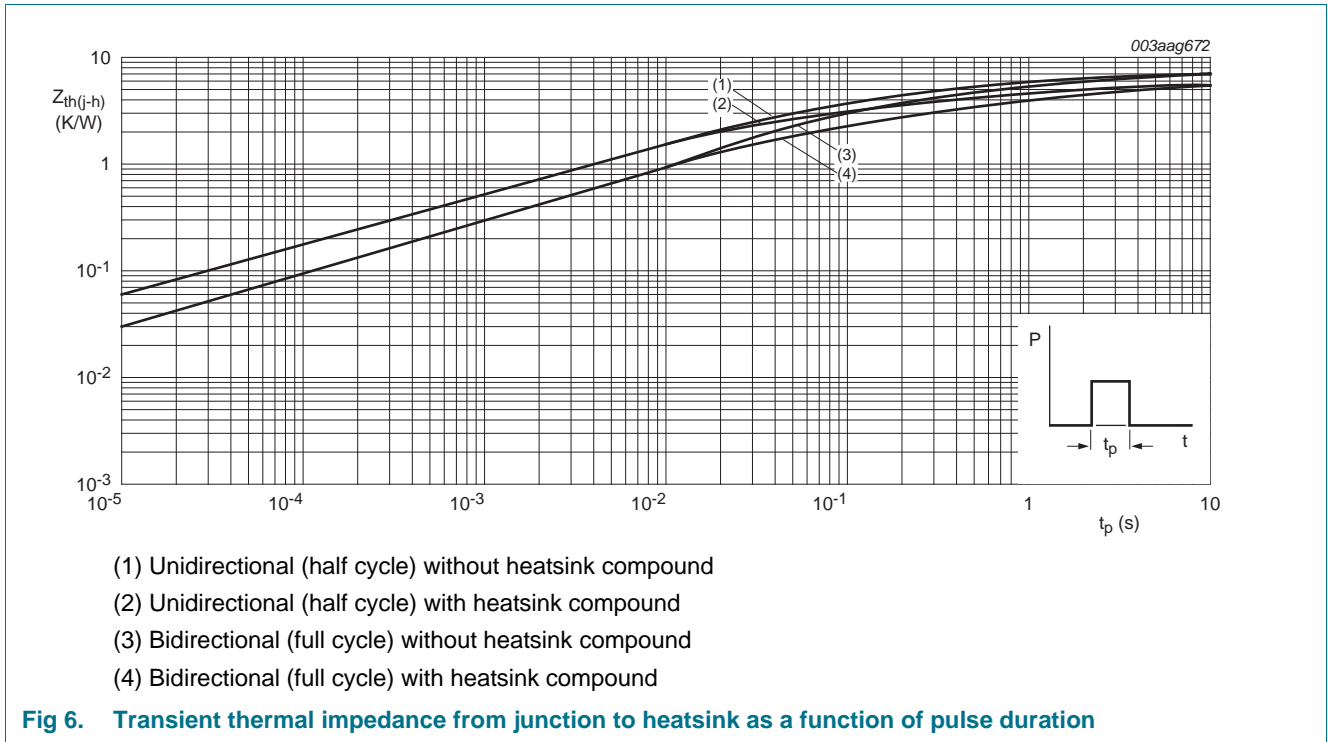
Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	full or half cycle; with heatsink compound; see Figure 6	-	-	5.5	K/W
		full or half cycle; without heatsink compound; see Figure 6	-	-	7.2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W



6. Isolation characteristics

Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free ; $50\text{ Hz} \leq f \leq 60\text{ Hz}$; $RH \leq 65\%$; $T_h = 25\text{ }^\circ\text{C}$	-	-	2500	V
C_{isol}	isolation capacitance	from main terminal 2 to external heatsink ; $f = 1\text{ MHz}$; $T_h = 25\text{ }^\circ\text{C}$	-	10	-	pF

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; see Figure 7	-	-	10	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; see Figure 7	-	-	10	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ °C}$; see Figure 7	-	-	10	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G+; $T_j = 25\text{ °C}$; see Figure 7	-	-	25	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; see Figure 8	-	-	15	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; see Figure 8	-	-	25	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ °C}$; see Figure 8	-	-	15	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G+; $T_j = 25\text{ °C}$; see Figure 8	-	-	15	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ °C}$; see Figure 9	-	-	15	mA
V_T	on-state voltage	$I_T = 6\text{ A}$; $T_j = 25\text{ °C}$; see Figure 10	-	1.3	1.5	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ °C}$; see Figure 11	-	0.7	1.5	V
		$V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 125\text{ °C}$; see Figure 11	0.25	0.4	-	V
I_D	off-state current	$V_D = 600\text{ V}$; $T_j = 125\text{ °C}$	-	0.1	0.5	mA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}$; $T_j = 125\text{ °C}$; exponential waveform; gate open circuit	80	-	-	V/ μ s
dV_{com}/dt	rate of change of commutating voltage	$V_D = 400\text{ V}$; $T_j = 125\text{ °C}$; $dI_{com}/dt = 1.8\text{ A/ms}$; $I_T = 4\text{ A}$; gate open circuit	15	-	-	V/ μ s
dI_{com}/dt	rate of change of commutating current	$V_D = 400\text{ V}$; $I_{T(RMS)} = 4\text{ A}$; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$; (snubberless condition); gate open circuit	1.5	-	-	A/ms
t_{gt}	gate-controlled turn-on time	$I_{TM} = 6\text{ A}$; $V_D = 600\text{ V}$; $I_G = 0.1\text{ A}$; $dI_G/dt = 5\text{ A}/\mu\text{s}$	-	2	-	μ s

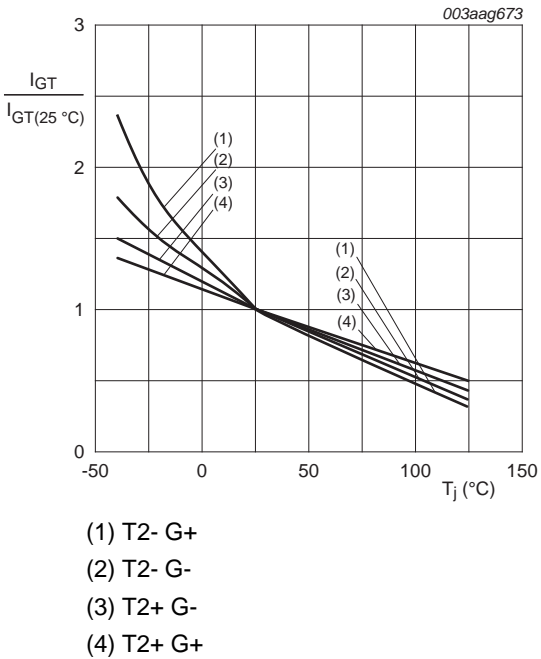


Fig 7. Normalized gate trigger current as a function of junction temperature

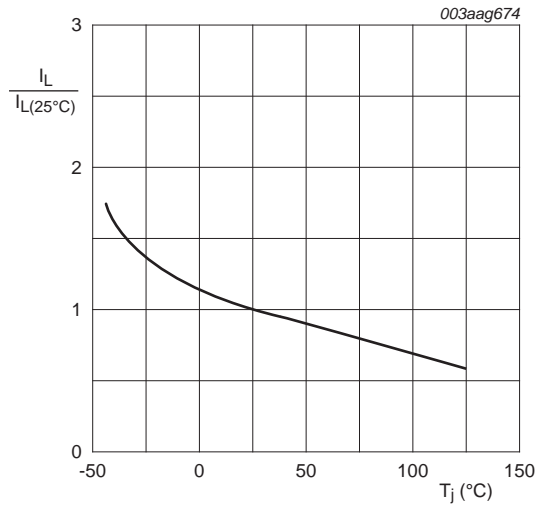


Fig 8. Normalized latching current as a function of junction temperature

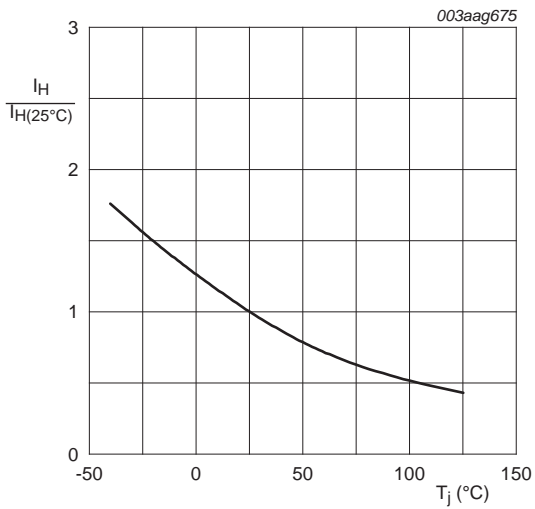
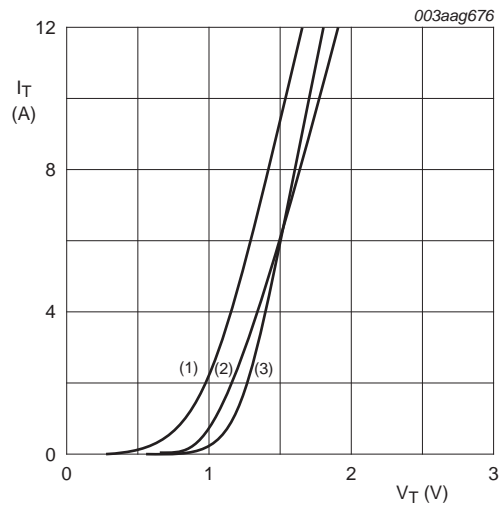


Fig 9. Normalized holding current as a function of junction temperature



$V_o = 1.035\text{ V}$; $R_s = 0.078\ \Omega$
 Fig 10. On-state current as a function of on-state voltage

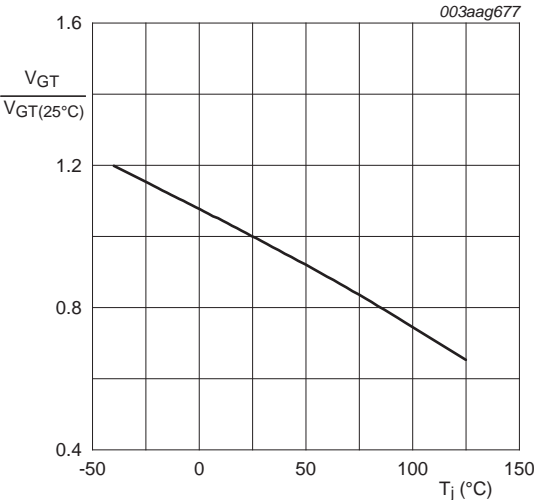


Fig 11. Normalized gate trigger voltage as a function of junction temperature

8. Package outline

Plastic single-ended package; isolated heatsink mounted;
1 mounting hole; 3-lead TO-220 'full pack'

SOT186A

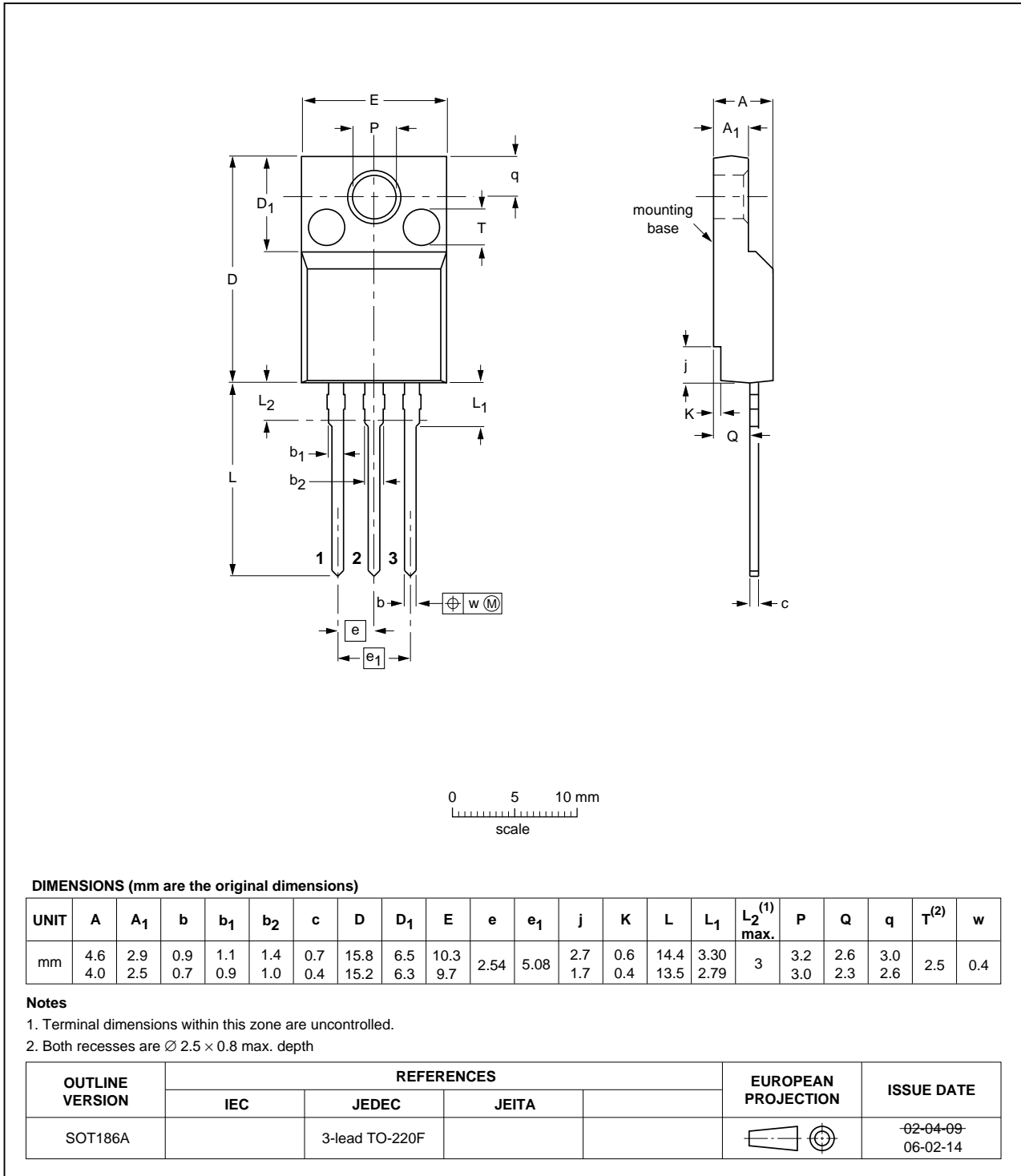


Fig 12. Package outline SOT186A (TO-220F)

9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BT234X-600E v.1	20111012	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status ^[1] ^[2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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